

isc N-Channel MOSFET Transistor

AOTF20N60

FEATURES

- Drain Current –I_D= 20A@ T_C=25 $^\circ\!\mathrm{C}$
- Drain Source Voltage-: V_{DSS}=600V(Min)
- Static Drain-Source On-Resistance : R_{DS(on)} =0.37 Ω (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

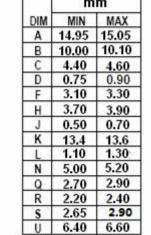
DESCRIPTION

• Designed for use in switch mode power supplies and general purpose applications.

| ABSOLUTE WAXIWUW KATINGS(Ta=25 C) | | | | | | |
|-----------------------------------|---|-------|------|--|--|--|
| SYMBOL | PARAMETER | VALUE | UNIT | | | |
| V _{DSS} | Drain-Source Voltage | 600 | V | | | |
| V_{GS} | Gate-Source Voltage-Continuous | ±30 | V | | | |
| ID | Drain Current-Continuous | 20 | А | | | |
| I _{DM} | Drain Current-Single Pluse | 80 | А | | | |
| P _D | Total Dissipation @T _c =25℃ | 50 | W | | | |
| TJ | Max. Operating Junction Temperature -55~150 | | °C | | | |
| T _{stg} | Storage Temperature -55~150 | | °C | | | |

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

pin 1.Gate 2.Drain 3.Source TO-220F package



THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|--------------------------------------|-----|------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 2.5 | °C/W |

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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | МАХ | UNIT |
|----------------------|---------------------------------|---|-----|---------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D = 0.25mA | 600 | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} ; I _D = 0.25mA | 3.2 | 4.5 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =10A | | 0.37 | Ω |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±30V;V _{DS} = 0 | | ±100 | nA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =600V; V _{GS} = 0 V _{DS} =480V; V _{GS} = 0@T _J =125℃ | | 1 10 | μA |
| V _{SD} | Forward On-Voltage | I _S = 1A; V _{GS} = 0 | | 1.0 | V |



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